

Do NOT Enter, as being non-compliant
11/30/06 JSR

10/768,515

F0773/AMDP999US

Proposed

AMENDMENTS TO THE SPECIFICATION

Filed
Electronically
11/6/06

In the Specification:

Please amend the Abstract of the Disclosure as follows:

A system and method are provided to extend the resolution normally achievable with nanoprint lithography processes to facilitate the reproduction small features required for the production of integrated circuits. ~~The present invention provides for creation of a~~
~~A translucent mask (or mold) is created~~ with three-dimensional features. The vertical dimension of the three-dimensional features can be characterized as sidewalls. ~~The present invention provides for depositing a~~ ~~A~~ light absorbing material ~~is deposited~~ as a thin film onto the surface of the mask or mold. After deposition of the light absorbing material the mask is further processed by etching or other similar techniques to remove the absorbing material ~~from~~ ~~from~~ all horizontal surfaces, leaving only a thin coating of the absorbing material on the vertical sidewalls of the features on the mask. ~~When a resist layer of a substrate is exposed by light passing through the mask, areas of the resist layer corresponding to locations of the vertical sidewalls of the mask~~ ~~The resist layer coating the sidewalls~~ will not be exposed as light in these areas is absorbed by the absorbing material. ~~The balance of the resist layer will be exposed as light passes through the mask unobstructed.~~ ~~Exposure of the resist coated substrate leaves the resist either more soluble or less soluble in a particular solvent depending upon the resist.~~ ~~Further development of the resist and processing of the substrate results in either the removal or the retention of small areas corresponding to the thickness of the light absorbing materials deposited on the sidewalls of the features on the mask.~~

Please amend the paragraph at page 9, lines 19-30 as follows:

However, the situation is different for light rays 808, 812, 818 and 822. Each of these light rays enters the translucent substrate 800 at its upper surface 830. However, instead of passing through the mask uninterrupted, each of these light rays is absorbed

10/768,515

F0773/AMDP999US

by light absorbing material 860 which has been deposited on the sidewalls of features on the mask. For example, light ray 808 enters mask 800 through the upper surface 830 of the mask. The light passes through the upper portion of the mask until it is absorbed by light absorbing material 860 which has been deposited onto sidewall 862. The situation for light rays 812, 818 and 822 are all similar in that each light ray encounters light absorbing material 860 deposited onto the sidewall of a three-dimensional feature. As a result, the portions of resist 882 852 located directly below the light absorbing material deposited onto the sidewalls of the three dimensional features are not exposed by light. In Fig. 8, the unexposed areas are 870, 872, 874 and 876.